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7/2017—Rev. E to Rev. F

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5/2017-Rev. D to Rev. E

Changes to Table 147

9/2016—Rev. C to Rev. D

Changed 3.0 V to 3.3 V and 2.7 V to 3.0 V	. Throughout
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2/2012-Rev. B to Rev. C

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10/2011—Rev. A to Rev. B

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8/2011-Rev. 0 to Rev. A

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4/2009—Revision 0: Initial Version

SPECIFICATIONS

ELECTRICAL CHARACTERISTICS—5 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = V_{DD2} = 5$ V. Minimum/maximum specifications apply over the entire recommended operation range of 4.5 V $\leq V_{DD1} \leq 5.5$ V, 4.5 V $\leq V_{DD2} \leq 5.5$ V, and -40° C $\leq T_A \leq 105^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

Table 1.

			A Grad	e		B Grade		C Grade				
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
SWITCHING SPECIFICATIONS												
Data Rate				1			10			90	Mbps	Within PWD limit
Propagation Delay	t _{PHL} , t _{PLH}	50	65	100	20	32	50	18	27	32	ns	50% input to 50% output
Pulse Width Distortion	PWD			40			3		0.5	2	ns	t _{PLH} — t _{PHL}
Change vs. Temperature			11			5			3		ps/°C	
Pulse Width	PW	1000			100			11.1			ns	Within PWD limit
Propagation Delay Skew	t _{PSK}			50			15			10	ns	Between any two units
Channel Matching												
Codirectional	t _{PSKCD}			50			3			2	ns	
Opposing-Direction	t _{PSKOD}			50			6			5	ns	

Table 2.

		1 Mb	ps—A, B,	C Grades	10 Mbps—B, C Grades			90 M	bps—C	Grade		
Parameter	Symbol	Min	Тур	Max	Min	Тур	Мах	Min	Тур	Max	Unit	Test Conditions
SUPPLY CURRENT												
ADuM4400	I _{DD1}		2.9	3.5		9.0	11.6		72	100	mA	
	I _{DD2}		1.2	1.9		3.0	5.5		19	36	mA	
ADuM4401	I _{DD1}		2.5	3.2		7.4	10.6		59	82	mA	
	I _{DD2}		1.6	2.4		4.4	6.5		32	46	mA	
ADuM4402	I _{DD1}		2.0	2.8		6.0	7.5		51	62	mA	
	I _{DD2}		2.0	2.8		6.0	7.5		51	62	mA	

Table 3. For All Models

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
DC SPECIFICATIONS						
Logic High Input Threshold	VIH	2.0			V	
Logic Low Input Threshold	VIL			0.8	V	
Logic High Output Voltage	V _{OH}	$V_{DDx} - 0.1$	5.0		V	$I_{Ox} = -20 \ \mu A$, $V_{Ix} = V_{IxH}$
		$V_{DDx} - 0.4$	4.8		V	$I_{Ox} = -3.2 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Voltage	Vol		0.0	0.1	V	$I_{Ox} = 20 \ \mu A$, $V_{Ix} = V_{IxL}$
			0.04	0.1	V	$I_{Ox} = 400 \ \mu A$, $V_{Ix} = V_{IxL}$
			0.2	0.4	V	$I_{Ox} = 3.2 \text{ mA}, V_{Ix} = V_{IxL}$
Input Current per Channel	l,	-10	+0.01	+10	μA	$0 \; V \leq V_{lx} \leq V_{\text{DDx}}$
Supply Current per Channel						
Quiescent Input Supply Current	I _{DDI(Q)}		0.57	0.83	mA	
Quiescent Output Supply Current	I _{DDO(Q)}		0.23	0.35	mA	
Dynamic Input Supply Current	I _{DDI(D)}		0.20		mA/Mbps	
Dynamic Output Supply Current	I _{DDO(D)}		0.05		mA/Mbps	
AC SPECIFICATIONS						
Output Rise/Fall Time	t _R /t _F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ¹	CM	25	35		kV/μs	$\label{eq:Vix} \begin{split} V_{\text{Ix}} = V_{\text{DDx}}, V_{\text{CM}} = 1000 \text{ V},\\ transient magnitude = 800 \text{ V} \end{split}$
Output Disable Propagation Delay	t _{PHZ} , t _{PLH}		6	8	ns	High/low-to-high impedance
Output Enable Propagation Delay	t _{PZH} , t _{PZL}		6	8	ns	High impedance-to-high/low
Refresh Rate	fr		1.2		Mbps	

¹ [CM] is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8 V_{DD}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

ELECTRICAL CHARACTERISTICS—3.3 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = V_{DD2} = 3.3$ V. Minimum/maximum specifications apply over the entire recommended operation range: 3.0 V $\leq V_{DD1} \leq 3.6$ V, 3.0 V $\leq V_{DD2} \leq 3.6$ V, and -40° C $\leq T_A \leq 105^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

Table 4.

			A Grad	e		B Grade		C Grade				
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
SWITCHING SPECIFICATIONS												
Data Rate				1			10			90	Mbps	Within PWD limit
Propagation Delay	tphl, tplh	50	75	100	20	38	50	20	34	45	ns	50% input to 50% output
Pulse Width Distortion	PWD			40			3		0.5	2	ns	$ t_{PLH} - t_{PHL} $
Change vs. Temperature			11			5			3		ps/°C	
Pulse Width	PW	1000			100			11.1			ns	Within PWD limit
Propagation Delay Skew	t PSK			50			22			16	ns	Between any two units
Channel Matching												
Codirectional	t pskcd			50			3			2	ns	
Opposing-Direction	t _{PSKOD}			50			6			5	ns	

Table 5.

		1 Mbp	os—A, B,	C Grades	10 MI	ops—B, (C Grades	90 M	bps—C	Grade		
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
SUPPLY CURRENT												
ADuM4400	I _{DD1}		1.6	2.1		4.8	7.1		37	54	mA	
	I _{DD2}		0.7	1.2		1.8	2.3		11	15	mA	
ADuM4401	I _{DD1}		1.4	1.9		0.1	5.6		31	44	mA	
	I _{DD2}		0.9	1.5		2.5	3.3		17	24	mA	
ADuM4402	I _{DD1}		1.2	1.7		3.3	4.4		24	39	mA	
	I _{DD2}		1.2	1.7		3.3	4.4		24	39	mA	

Table 6. For All Models

Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
DC SPECIFICATIONS						
Logic High Input Threshold	VIH	1.6			V	
Logic Low Input Threshold	VIL			0.4	V	
Logic High Output Voltage	Vон	V _{DDx} - 0.1	3.0		V	$I_{Ox} = -20 \ \mu A$, $V_{Ix} = V_{IxH}$
		$V_{DDx} - 0.4$	2.8		V	$I_{0x} = -3.2 \text{ mA}, V_{1x} = V_{1xH}$
Logic Low Output Voltage	Vol		0.0	0.1	V	$I_{Ox} = 20 \ \mu A, V_{Ix} = V_{IxL}$
			0.04	0.1	V	$I_{Ox} = 400 \ \mu A, V_{Ix} = V_{IxL}$
			0.2	0.4	V	$I_{Ox} = 3.2 \text{ mA}, V_{Ix} = V_{IxL}$
Input Current per Channel	h	-10	+0.01	+10	μA	$0~V \leq V_{\text{lx}} \leq V_{\text{DDx}}$
Supply Current per Channel						
Quiescent Input Supply Current	I _{DDI(Q)}		0.31	0.49	mA	
Quiescent Output Supply Current	I _{DDO(Q)}		0.19	0.27	mA	
Dynamic Input Supply Current	I _{DDI(D)}		0.10		mA/Mbps	
Dynamic Output Supply Current	I _{DDO(D)}		0.03		mA/Mbps	
AC SPECIFICATIONS						
Output Rise/Fall Time	t _R /t _F		3		ns	10% to 90%
Common-Mode Transient Immunity ¹	CM	25	35		kV/µs	$V_{lx} = V_{DDx}$, $V_{CM} = 1000$ V, transient magnitude = 800 V
Output Disable Propagation Delay	tphz, tplh		6	8	ns	High/low-to-high impedance
Output Enable Propagation Delay	t _{PZH} , t _{PZL}		6	8	ns	High impedance-to-high/low
Refresh Rate	fr		1.2		Mbps	

¹ [CM] is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8 V_{DD}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

ELECTRICAL CHARACTERISTICS—MIXED 5 V/3.3 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = 5$ V, $V_{DD2} = 3.3$ V. Minimum/maximum specifications apply over the entire recommended operation range: $4.5 \text{ V} \le V_{DD1} \le 5.5 \text{ V}$, $3.0 \text{ V} \le V_{DD2} \le 3.6 \text{ V}$, and -40° C $\le T_A \le 105^{\circ}$ C, unless otherwise noted. Switching specifications are tested with $C_L = 15 \text{ pF}$ and CMOS signal levels, unless otherwise noted.

Table 7.

			A Grade			B Grad	e	C Grade				
Parameter	Symbol	Min	Тур	Мах	Min	Тур	Мах	Min	Тур	Мах	Unit	Test Conditions
SWITCHING SPECIFICATIONS												
Data Rate				1			10			90	Mbps	Within PWD limit
Propagation Delay	t _{PHL} , t _{PLH}	50	70	50	15	35	50	20	30	40	ns	50% input to 50% output
Pulse Width Distortion	PWD			40			3		0.5	2	ns	tplh — tphl
Change vs. Temperature			11			5			3		ps/°C	
Pulse Width	PW	1000			100			11.1			ns	Within PWD limit
Propagation Delay Skew	t PSK			50			22			14	ns	Between any two units
Channel Matching												
Codirectional	t PSKCD			50			3			2	ns	
Opposing-Direction	t _{PSKOD}			50			6			5	ns	

Table 8.

		1 Mbj	ps—A, B,	C Grades	10 M	bps—B, (C Grades	90 M	bps—C	Grade		
Parameter	Symbol	Min	Тур	Max	Min	Тур	Мах	Min	Тур	Max	Unit	Test Conditions
SUPPLY CURRENT												
ADuM4400	I _{DD1}		2.9	3.5		9.0	11.6		72	100	mA	
	I _{DD2}		0.7	1.2		1.8	2.3		11	15	mA	
ADuM4401	I _{DD1}		2.5	3.2		7.4	10.6		59	82	mA	
	I _{DD2}		0.9	1.5		2.5	3.3		17	24	mA	
ADuM4402	I _{DD1}		2.0	2.8		6.0	7.5		46	62	mA	
	I _{DD2}		1.2	1.7		3.3	4.4		24	39	mA	

Table 9. For All Models

Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
DC SPECIFICATIONS						
Logic High Input Threshold	VIH	2.0			V	
Logic Low Input Threshold	VIL			0.8	V	
Logic High Output Voltage	Vон	V _{DDx} - 0.1	3.0		V	$I_{Ox} = -20 \ \mu A$, $V_{Ix} = V_{IxH}$
		V _{DDx} -0.4	2.8		V	$I_{Ox} = -3.2 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Voltage	Vol		0.0	0.1	V	$I_{\text{Ox}} = 20 \; \mu\text{A}, V_{\text{Ix}} = V_{\text{IxL}}$
			0.04	0.1	V	$I_{\text{Ox}} = 400 \; \mu\text{A} \text{, } V_{\text{Ix}} = V_{\text{IxL}}$
			0.2	0.4	V	$I_{\text{Ox}} = 3.2 \text{ mA}, V_{\text{Ix}} = V_{\text{IxL}}$
Input Current per Channel	h	-10	+0.01	+10	μA	$0~V \leq V_{lx} \leq V_{DDx}$
Supply Current per Channel						
Quiescent Input Supply Current	I _{DDI(Q)}		0.57	0.83	mA	
Quiescent Output Supply Current	IDDO(Q)		0.29	0.27	mA	
Dynamic Input Supply Current	DDI(D)		0.20		mA/Mbps	
Dynamic Output Supply Current	I _{DDO(D)}		0.03		mA/Mbps	
AC SPECIFICATIONS						
Output Rise/Fall Time	t _R /t _F		3		ns	10% to 90%
Common-Mode Transient Immunity ¹	CM	25	35		kV/μs	$V_{lx} = V_{DDx}, V_{CM} = 1000 V,$ transient magnitude = 800 V
Output Disable Propagation Delay	tphz, tplh		6	8	ns	High/low-to-high impedance
Output Enable Propagation Delay	t _{PZH} , t _{PZL}		6	8	ns	High impedance-to-high/low
Refresh Rate	fr		1.2		Mbps	

 1 [CM] is the maximum common-mode voltage slew rate that can be sustained while maintaining V₀ > 0.8 V_{DD}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

ELECTRICAL CHARACTERISTICS—MIXED 3.3 V/5 V OPERATION

All typical specifications are at $T_A = 25^{\circ}$ C, $V_{DD1} = 3.3$ V, $V_{DD2} = 5$ V. Minimum/maximum specifications apply over the entire recommended operation range: 3.0 V \leq V_{DD1} \leq 3.6 V, 4.5 V \leq V_{DD2} \leq 5.5 V, and -40°C \leq T_A \leq +105°C, unless otherwise noted. Switching specifications are tested with $C_L = 15$ pF and CMOS signal levels, unless otherwise noted.

Table 10.

			A Grad	e	I	B Grad	e		C Grad	e		
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
SWITCHING SPECIFICATIONS												
Data Rate				1			10			90	Mbps	Within PWD limit
Propagation Delay	tphl, tplh	50	70	100	15	35	50	20	30	40	ns	50% input to 50% output
Pulse Width Distortion	PWD			40			3		0.5	2	ns	$ t_{PLH} - t_{PHL} $
Change vs. Temperature			11			5			3		ps/°C	
Pulse Width	PW	1000			100			11.1			ns	Within PWD limit
Propagation Delay Skew	t PSK			50			22			14	ns	Between any two units
Channel Matching												
Codirectional	t pskcd			50			3			2	ns	
Opposing-Direction	t _{PSKOD}			50			6			5	ns	

Table 11.

		1 MB	ps—A, B	, C Grades	10 N	1Bps—B	, C Grades	90 M	Bps—C	Grade		
Parameter	Symbol	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit	Test Conditions
SUPPLY CURRENT												
ADuM4400	I _{DD1}		1.6	2.1		4.8	7.1		37	54	mA	
	I _{DD2}		1.2	1.9		3.0	5.5		19	36	mA	
ADuM4401	I _{DD1}		1.4	1.9		4.1	5.6		31	44	mA	
	I _{DD2}		1.6	2.4		4.4	6.5		32	46	mA	
ADuM4402	I _{DD1}		1.2	1.7		3.3	4.4		24	39	mA	
	I _{DD2}		2.0	2.8		6.0	7.5		46	62	mA	

Table 12. For All Models

Parameter	Symbol	Min	Тур	Мах	Unit	Test Conditions
DC SPECIFICATIONS						
Logic High Input Threshold	VIH	1.6			V	
Logic Low Input Threshold	VIL			0.4	V	
Logic High Output Voltage	Vон	V _{DDx} - 0.1	5.0		V	$I_{\text{Ox}} = -20 \ \mu\text{A}, V_{\text{Ix}} = V_{\text{IxH}}$
		$V_{DDx} - 0.4$	4.8		V	$I_{Ox} = -3.2 \text{ mA}, V_{Ix} = V_{IxH}$
Logic Low Output Voltage	Vol		0.0	0.1	V	$I_{Ox} = 20 \ \mu A$, $V_{Ix} = V_{IxL}$
			0.04	0.1	V	$I_{\text{Ox}} = 400 \; \mu\text{A}, V_{\text{Ix}} = V_{\text{IxL}}$
			0.2	0.4	V	$I_{Ox} = 3.2 \text{ mA}, V_{Ix} = V_{IxL}$
Input Current per Channel	h	-10	+0.01	+10	μΑ	$0~V \leq V_{lx} \leq V_{DDx}$
Supply Current per Channel						
Quiescent Input Supply Current	I _{DDI(Q)}		0.31	0.49	mA	
Quiescent Output Supply Current	I _{DDO(Q)}		0.19	0.35	mA	
Dynamic Input Supply Current	I _{DDI(D)}		0.10		mA/Mbps	
Dynamic Output Supply Current	I _{DDO(D)}		0.05		mA/Mbps	
AC SPECIFICATIONS						
Output Rise/Fall Time	t _R /t _F		2.5		ns	10% to 90%
Common-Mode Transient Immunity ¹	CM	25	35		kV/µs	$V_{Ix} = V_{DDx}$, $V_{CM} = 1000 V$, transient magnitude = 800 V
Output Disable Propagation Delay	t _{PHZ} , t _{PLH}		6	8	ns	High/low-to-high impedance
Output Enable Propagation Delay	t _{PZH} , t _{PZL}		6	8	ns	High impedance-to-high/low
Refresh Rate	fr		1.1		Mbps	

¹ |CM| is the maximum common-mode voltage slew rate that can be sustained while maintaining V_o > 0.8 V_{DD}. The common-mode voltage slew rates apply to both rising and falling common-mode voltage edges.

PACKAGE CHARACTERISTICS

Table 13.

Parameter	Symbol	Min	Тур	Max	Unit	Test Conditions
Resistance (Input to Output) ¹	RI-O		10 ¹²		Ω	
Capacitance (Input to Output) ¹	CI-O		2.2		pF	f = 1 MHz
Input Capacitance ²	Cı		4.0		рF	
IC Junction-to-Case Thermal Resistance, Side 1	θ」		33		°C/W	Thermocouple located at
IC Junction-to-Case Thermal Resistance, Side 2	θ _{JCO}		28		°C/W	center of package underside

¹ Device considered a 2-terminal device: Pin 1, Pin 2, Pin 3, Pin 4, Pin 5, Pin 6, Pin 7, and Pin 8 shorted together and Pin 9, Pin 10, Pin 11, Pin 12, Pin 13, Pin 14, Pin 15, and Pin 16 shorted together.

² Input capacitance is from any input data pin to ground.

REGULATORY INFORMATION

The ADuM440x are approved by the organizations listed in Table 14. Refer to Table 19 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

UL	CSA	VDE	CQC
Recognized under 1577 Component Recognition Program ¹	Approved under CSA Component Acceptance Notice #5A	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10): 2006- 12 ²	Approved under CQC11-471543-2015
Single Protection 5000 V rms Isolation Voltage	Basic insulation per CSA 60950-1-07 and IEC60950-1, 600 V rms (848 V peak) maximumworking voltageRW-16 packageReinforced insulation per CSA 60950-1-07and IEC 60950-1, 380 V rms (537 V peak)maximum working voltage; reinforcedinsulation per IEC 60601-1 125 V rms(176 V peak) maximum working voltageRI-16 packageReinforced insulation per CSA 60950-1-07and IEC 60950-1, 400 V rms (565 V peak)maximum working voltage; reinforcedinsulation per IEC 60601-1 250 V rms	Reinforced insulation, 846 V peak	RW-16 package Basic insulation per GB4943.1-2011, 760 V rms (1075 V peak) maximum working voltage, tropical climate, altitude ≤ 5000 m Reinforced insulation per GB4943.1-2011, 380 V rms (537 V peak) maximum working voltage, tropical climate, altitude ≤ 5000 m RI-16 Package Basic insulation per GB4943.1-2011, 820 V rms (1159 V peak) maximum working voltage, tropical climate, altitude ≤ 5000 m
	(353 V peak) maximum working voltage		Reinforced insulation per GB4943.1-2011, 401 V rms (578 V peak) maximum working voltage, tropical climate, altitude ≤ 5000 m
File E214100	File 205078	File 2471900-4880-0001	File CQC16001150402

¹ In accordance with UL1577, each ADuM440x is proof tested by applying an insulation test voltage ≥ 6000 V rms for 1 second (current leakage detection limit = 10 μA).
² In accordance with DIN V VDE V 0884-10, each ADuM440x is proof tested by applying an insulation test voltage ≥1590 V peak for 1 sec (partial discharge detection limit = 5 pC). The * marking branded on the component designates DIN V VDE V 0884-10 approval.

INSULATION AND SAFETY-RELATED SPECIFICATIONS

Table 15.

Parameter	Symbol	Value	Unit	Conditions
Rated Dielectric Insulation Voltage		5000	V rms	1-minute duration
Minimum External Air Gap	L(I01)	8.0 min	mm	Distance measured from input terminals to output terminals, shortest distance through air along the PCB mounting plane, as an aid to PC board layout
Minimum External Tracking (Creepage) RW-16 Package	L(102)	7.7 min	mm	Measured from input terminals to output terminals, shortest distance path along body
Minimum External Tracking (Creepage) RI-16 Package	L(102)	8.3 min	mm	Measured from input terminals to output terminals, shortest distance path along body
Minimum Internal Gap (Internal Clearance)		0.017 min	mm	Insulation distance through insulation
Tracking Resistance (Comparative Tracking Index)	СТІ	>175	V	DIN IEC 112/VDE 0303 Part 1

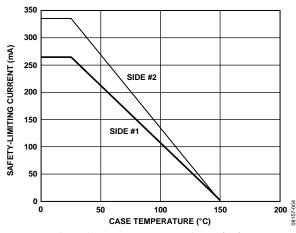
DIN V VDE V 0884-10 (VDE V 0884-10) INSULATION CHARACTERISTICS

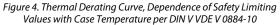
These isolators are suitable for reinforced electrical isolation only within the safety limit data. Maintenance of the safety data is ensured by means of protective circuits.

Note that the * marking on packages denotes DIN V VDE V 0884-10 approval for 846 V peak working voltage.

Table	16.
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Description	Conditions	Symbol	Characteristic	Unit
Installation Classification per DIN VDE 0110				
For Rated Mains Voltage ≤ 300 V rms			l to IV	
For Rated Mains Voltage ≤ 450 V rms			l to ll	
For Rated Mains Voltage \leq 600 V rms			l to ll	
Climatic Classification			40/105/21	
Pollution Degree (DIN VDE 0110, Table 1)			2	
Maximum Working Insulation Voltage		VIORM	846	V peak
Input-to-Output Test Voltage, Method b1	$V_{IORM} \times 1.875 = V_{PR}$, 100% production test, $t_m = 1$ sec, partial discharge < 5 pC	V _{PR}	1590	V peak
Input-to-Output Test Voltage, Method a		V _{PR}		
After Environmental Tests Subgroup 1	$V_{IORM} \times 1.6 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC		1375	V peak
After Input and/or Safety Test Subgroup 2 and Subgroup 3	$V_{IORM} \times 1.2 = V_{PR}$, $t_m = 60$ sec, partial discharge < 5 pC		1018	V peak
Highest Allowable Overvoltage	Transient overvoltage, $t_{TR} = 10$ seconds	VTR	6000	V peak
Safety-Limiting Values	Maximum value allowed in the event of a failure; see Figure 4			
Case Temperature		Ts	150	°C
Side 1 Current		I _{S1}	265	mA
Side 2 Current		Is ₂	335	mA
Insulation Resistance at Ts	$V_{IO} = 500 V$	Rs	>109	Ω





RECOMMENDED OPERATING CONDITIONS

Table 17.				
Parameter	Symbol	Min	Мах	Unit
Operating Temperature	TA	-40	+105	°C
Supply Voltages ¹	V_{DD1}, V_{DD2}	3.0	5.5	V
Input Signal Rise and Fall Times			1.0	ms

¹ All voltages are relative to their respective ground.

ABSOLUTE MAXIMUM RATINGS

Table 18.

Parameter	Rating		
Storage Temperature (T _{ST})	–65°C to +150°C		
Ambient Operating Temperature (T _A)	-40°C to +105°C		
Supply Voltages (V _{DD1} , V _{DD2}) ¹	–0.5 V to +7.0 V		
Input Voltage (V_{IA} , V_{IB} , V_{IC} , V_{ID} , V_{E1} , V_{E2}) ^{1, 2}	-0.5 V to V _{DDI} + 0.5 V		
Output Voltage (V _{OA} , V _{OB} , V _{OC} , V _{OD}) ^{1, 2}	-0.5 V to V _{DDO} + 0.5 V		
Average Output Current Per Pin ³			
Side 1 (I ₀₁)	–18 mA to +18 mA		
Side 2 (I _{O2})	–22 mA to +22 mA		
Common-Mode Transients ⁴	–100 kV/μs to +100 kV/μs		

¹ All voltages are relative to their respective ground.

 2 V_{\text{DD}} and V_{\text{DD}} refer to the supply voltages on the input and output sides of a given channel, respectively. See the PC Board Layout section.

³ See Figure 4 for maximum rated current values for various temperatures.
 ⁴ Refers to common-mode transients across the insulation barrier. Common-mode transients exceeding the Absolute Maximum Rating can cause latch-up or permanent damage.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

ESD CAUTION



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Table 19. Maximum Continuous Working Voltage¹

Parameter	Max	Unit	Constraint
AC Voltage, Bipolar Waveform	565	V peak	50 year minimum lifetime
AC Voltage, Unipolar Waveform			
Reinforced Insulation	846	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10
DC Voltage			
Reinforced Insulation	846	V peak	Maximum approved working voltage per IEC 60950-1 and VDE V 0884-10

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

Table 20. Truth Table (Positive Logic)

V _{Ix} Input ¹	V _{Ex} Input	V _{DDI} State ¹	V _{DDO} State ¹	Vox Output ¹	Notes
Н	H or NC	Powered	Powered	Н	
L	H or NC	Powered	Powered	L	
Х	L	Powered	Powered	Z	
Х	H or NC	Unpowered	Powered	н	Outputs return to input state within 1 μ s of V _{DD} power restoration.
Х	L	Unpowered	Powered	Z	
Х	х	Powered	Unpowered	Indeterminate	Outputs return to input state within 1 μ s of V _{DDO} power restoration if V _{Ex} state is H or NC. Outputs return to high impedance state within 8 ns of V _{DDO} power restoration if V _{Ex} state is L.

¹ V_k and V_{0x} refer to the input and output signals of a given channel (A, B, C, or D). V_{Ex} refers to the output enable signal on the same side as the V_{0x} outputs. V_{DDI} and V_{DDO} refer to the supply voltages on the input and output sides of the given channel, respectively.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

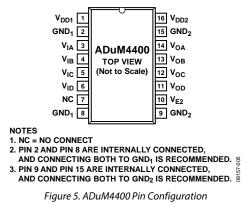
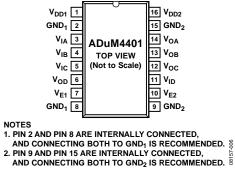


Table 21. ADuM4400 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2	GND1	Ground 1. Ground reference for isolator Side 1.
3	VIA	Logic Input A.
4	VIB	Logic Input B.
5	V _{IC}	Logic Input C.
6	VID	Logic Input D.
7	NC	No Connect.
8	GND1	Ground 1. Ground reference for isolator Side 1.
9	GND ₂	Ground 2. Ground reference for isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{Ox} outputs on Side 2 are enabled when V _{E2} is high or disconnected. V _{Ox} Side 2 outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	Vod	Logic Output D.
12	Voc	Logic Output C.
13	V _{OB}	Logic Output B.
14	Voa	Logic Output A.
15	GND ₂	Ground 2. Ground reference for isolator Side 2.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.



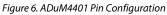
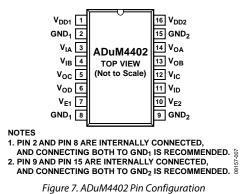


Table 22. ADuM4401 Pin Function Descriptions

Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2	GND1	Ground 1. Ground reference for isolator Side 1.
3	VIA	Logic Input A.
4	VIB	Logic Input B.
5	V _{IC}	Logic Input C.
6	Vod	Logic Output D.
7	V _{E1}	Output Enable. Active high logic input. V_{0x} Side 1 outputs are enabled when V_{E1} is high or disconnected. V_{0x} Side 1 outputs are disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.
8	GND1	Ground 1. Ground reference for isolator Side 1.
9	GND ₂	Ground 2. Ground reference for isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V _{Ox} outputs on Side 2 are enabled when V _{E2} is high or disconnected. V _{Ox} Side 2 outputs are disabled when V _{E2} is low. In noisy environments, connecting V _{E2} to an external logic high or low is recommended.
11	VID	Logic Input D.
12	Voc	Logic Output C.
13	Vов	Logic Output B.
14	V _{OA}	Logic Output A.
15	GND ₂	Ground 2. Ground reference for isolator Side 2.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.



Pin No.	Mnemonic	Description
1	V _{DD1}	Supply Voltage for Isolator Side 1, 3.0 V to 5.5 V.
2	GND1	Ground 1. Ground reference for isolator Side 1.
3	VIA	Logic Input A.
4	VIB	Logic Input B.
5	Voc	Logic Output C.
6	Vod	Logic Output D.
7	V _{E1}	Output Enable 1. Active high logic input. V_{Ox} Side 1 outputs are enabled when V_{E1} is high or disconnected. V_{OX} Side 1 outputs are disabled when V_{E1} is low. In noisy environments, connecting V_{E1} to an external logic high or low is recommended.
8	GND1	Ground 1. Ground reference for isolator Side 1.
9	GND ₂	Ground 2. Ground reference for isolator Side 2.
10	V _{E2}	Output Enable 2. Active high logic input. V_{Ox} outputs on Side 2 are enabled when V_{E2} is high or disconnected. V_{Ox} Side 2 outputs are disabled when V_{E2} is low. In noisy environments, connecting V_{E2} to an external logic high or low is recommended.
11	VID	Logic Input D.
12	VIC	Logic Input C.
13	Vob	Logic Output B.
14	VOA	Logic Output A.
15	GND ₂	Ground 2. Ground reference for isolator Side 2.
16	V _{DD2}	Supply Voltage for Isolator Side 2, 3.0 V to 5.5 V.

TYPICAL PERFORMANCE CHARACTERISTICS

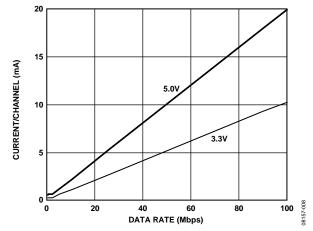


Figure 8. Typical Input Supply Current per Channel vs. Data Rate (No Load)

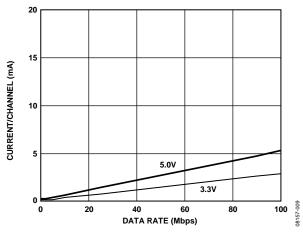


Figure 9. Typical Output Supply Current per Channel vs. Data Rate (No Load)

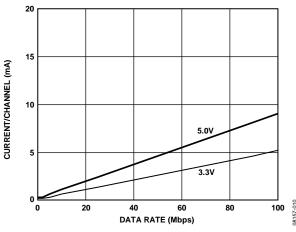


Figure 10. Typical Output Supply Current per Channel vs. Data Rate (15 pF Output Load)

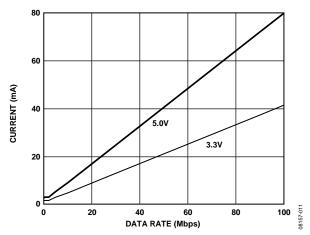


Figure 11. Typical ADuM4400 V_{DD1} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

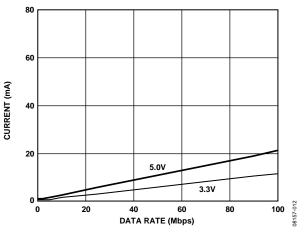


Figure 12. Typical ADuM4400 VDD2 Supply Current vs. Data Rate for 5 V and 3 V Operation

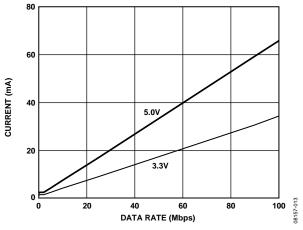


Figure 13. Typical ADuM4401 V_{DD1} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

Data Sheet

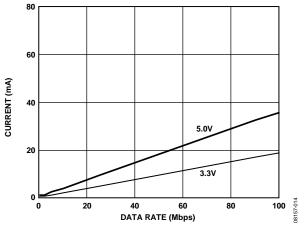


Figure 14. Typical ADuM4401 V_{DD2} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

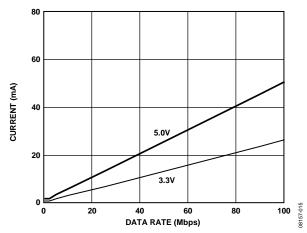


Figure 15. Typical ADuM4402 V_{DD1} or V_{DD2} Supply Current vs. Data Rate for 5 V and 3.3 V Operation

ADuM4400/ADuM4401/ADuM4402

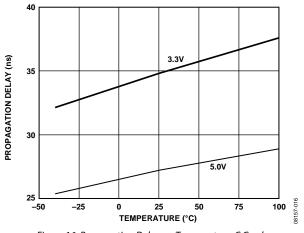


Figure 16. Propagation Delay vs. Temperature, C Grade

APPLICATIONS INFORMATION PC BOARD LAYOUT

The ADuM440x digital isolators require no external interface circuitry for the logic interfaces. Power supply bypassing is strongly recommended at the input and output supply pins (see Figure 17). Bypass capacitors are most conveniently connected between Pin 1 and Pin 2 for V_{DD1} and between Pin 15 and Pin 16 for V_{DD2} . The capacitor value should be between 0.01 μ F and 0.1 μ F. The total lead length between both ends of the capacitor and the input power supply pin should not exceed 20 mm. Bypassing between Pin 1 and Pin 8 and between Pin 9 and Pin 16 should also be considered unless the ground pair on each package side are connected close to the package.

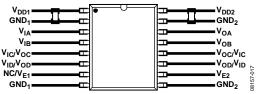


Figure 17. Recommended Printed Circuit Board Layout

In applications involving high common-mode transients, ensure that board coupling across the isolation barrier is minimized. Furthermore, the board layout should be designed such that any coupling that does occur equally affects all pins on a given component side. Failure to ensure this could cause voltage differentials between pins exceeding the Absolute Maximum Ratings of the device, thereby leading to latch-up or permanent damage.

See the AN-1109 Application Note for board layout guidelines.

SYSTEM-LEVEL ESD CONSIDERATIONS AND ENHANCEMENTS

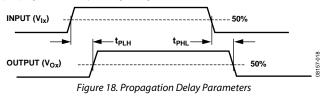
System-level ESD reliability (for example, per IEC 61000-4-x) is highly dependent on system design, which varies widely by application. The ADuM440x incorporate many enhancements to make ESD reliability less dependent on system design. The enhancements include

- ESD protection cells added to all input/output interfaces.
- Key metal trace resistances reduced using wider geometry and paralleling of lines with vias.
- The SCR effect, inherent in CMOS devices, minimized by using guarding and isolation techniques between PMOS and NMOS devices.
- Areas of high electric field concentration eliminated using 45° corners on metal traces.
- Supply pin overvoltage prevented with larger ESD clamps between each supply pin and its respective ground.

While the ADuM440x improve system-level ESD reliability, they are no substitute for a robust system-level design. See the AN-793 Application Note, ESD/Latch-Up Considerations with *iCoupler Isolation Products*, for detailed recommendations on board layout and system-level design.

PROPAGATION DELAY-RELATED PARAMETERS

Propagation delay is a parameter that describes the length of time for a logic signal to propagate through a component. The propagation delay to a logic low output can differ from the propagation delay to logic high.



Pulse width distortion is the maximum difference between these two propagation delay values and is an indication of how accurately the input signal's timing is preserved.

Channel-to-channel matching refers to the maximum amount the propagation delay differs among channels within a single ADuM440x component.

Propagation delay skew refers to the maximum amount the propagation delay differs among multiple ADuM440x components operated under the same conditions.

DC CORRECTNESS AND MAGNETIC FIELD IMMUNITY

Positive and negative logic transitions at the isolator input cause narrow (~1 ns) pulses to be sent via the transformer to the decoder. The decoder is bistable and is therefore either set or reset by the pulses, indicating input logic transitions. In the absence of logic transitions at the input for more than ~1 μ s, a periodic set of refresh pulses indicative of the correct input state are sent to ensure dc correctness at the output. If the decoder receives no internal pulses for more than approximately 5 μ s, the input side is assumed to be without power or nonfunctional; in which case, the isolator output is forced to a default state (see Table 20) by the watchdog timer circuit.

The limitation on the ADuM440x magnetic field immunity is set by the condition in which induced voltage in the transformer's receiving coil is large enough to either falsely set or reset the decoder. The following analysis defines the conditions under which this can occur. The 3 V operating condition of the ADuM440x is examined because it represents the most susceptible mode of operation. The pulses at the transformer output have an amplitude greater than 1.0 V. The decoder has a sensing threshold at about 0.5 V, thereby establishing a 0.5 V margin in which induced voltages can be tolerated. The voltage induced across the receiving coil is given by

 $V = (-d\beta/dt)\Sigma \prod r_n^2; n = 1, 2, ..., N$

where:

 β is the magnetic flux density (gauss).

N is the number of turns in the receiving coil.

 r_n is the radius of the nth turn in the receiving coil (cm).

Given the geometry of the receiving coil in the ADuM440x and an imposed requirement that the induced voltage be at most 50% of the 0.5 V margin at the decoder, a maximum allowable magnetic field is calculated as shown in Figure 19.

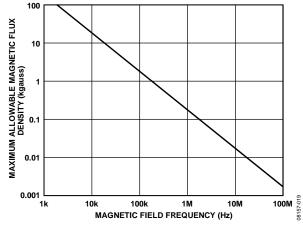
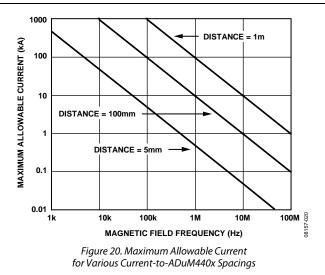


Figure 19. Maximum Allowable External Magnetic Flux Density

For example, at a magnetic field frequency of 1 MHz, the maximum allowable magnetic field of 0.2 kgauss induces a voltage of 0.25 V at the receiving coil. This is about 50% of the sensing threshold and does not cause a faulty output transition. Similarly, if such an event were to occur during a transmitted pulse (and was of the worst-case polarity), it would reduce the received pulse from >1.0 V to 0.75 V—still well above the 0.5 V sensing threshold of the decoder.

The preceding magnetic flux density values correspond to specific current magnitudes at given distances away from the ADuM440x transformers. Figure 20 expresses these allowable current magnitudes as a function of frequency for selected distances. As can be seen, the ADuM440x are immune and can be affected only by extremely large currents operated at high frequency and very close to the component. For the 1 MHz example noted, one would have to place a 0.5 kA current 5 mm away from the ADuM440x to affect the component's operation.

ADuM4400/ADuM4401/ADuM4402



Note that at combinations of strong magnetic field and high frequency, any loops formed by printed circuit board traces may induce sufficiently large error voltages to trigger the thresholds of succeeding circuitry. Care should be taken in the layout of such traces to avoid this possibility.

POWER CONSUMPTION

The supply current at a given channel of the ADuM440x isolator is a function of the supply voltage, the channel's data rate, and the channel's output load.

For each input channel, the supply current is given by

$$I_{DDI} = I_{DDI(Q)} \qquad \qquad f \le 0.5f$$

$$I_{DDI} = I_{DDI(D)} \times (2f - f_r) + I_{DDI(Q)}$$
 $f > 0.5f_r$

For each output channel, the supply current is given by:

$$\begin{split} I_{DDO} &= I_{DDO (Q)} & f \leq 0.5 f_r \\ I_{DDO} &= (I_{DDO (D)} + (0.5 \times 10^{-3}) \times C_L V_{DDO}) \times (2f - f_r) + I_{DDO (Q)} \\ & f > 0.5 f_r \end{split}$$

where:

*I*_{DDI (D)}, *I*_{DDO (D)} are the input and output dynamic supply currents per channel (mA/Mbps).

 C_L is the output load capacitance (pF).

 V_{DDO} is the output supply voltage (V).

f is the input logic signal frequency (MHz, half of the input data rate, NRZ signaling).

 f_r is the input stage refresh rate (Mbps).

 $I_{DDI(Q)}$, $I_{DDO(Q)}$ are the specified input and output quiescent supply currents (mA).

To calculate the total I_{DD1} and I_{DD2} , the supply currents for each input and output channel corresponding to I_{DD1} and I_{DD2} are calculated and totaled. Figure 8 and Figure 9 provide per channel supply currents as a function of data rate for an unloaded output condition. Figure 10 provides per channel supply current as a function of data rate for a 15 pF output condition. Figure 11 through Figure 15 provide total I_{DD1} and I_{DD2} as a function of data rate for ADuM4400/ADuM4401/ ADuM4402 channel configurations.

INSULATION LIFETIME

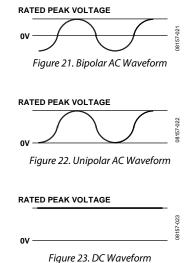
All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the ADuM440x.

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage. The values shown in Table 19 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition and the maximum CSA/VDE approved working voltages. In many cases, the approved working voltage is higher than the 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

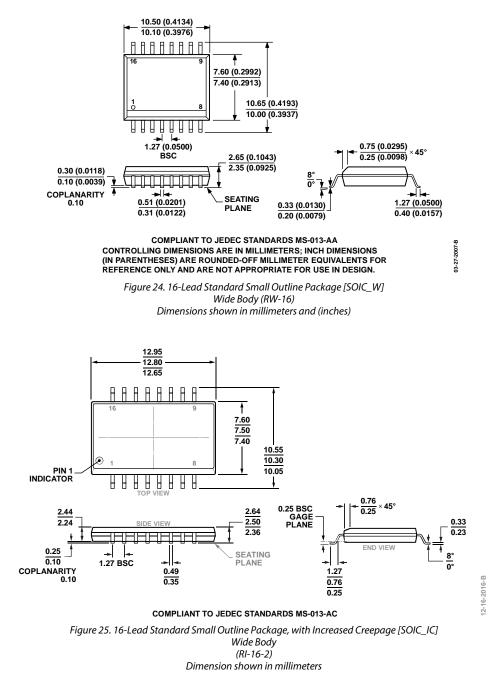
The insulation lifetime of the ADuM440x depends on the voltage waveform type imposed across the isolation barrier. The *i*Coupler insulation structure degrades at different rates, depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 21, Figure 22, and Figure 23 illustrate these different isolation voltage waveforms.

Bipolar ac voltage is the most stringent environment. The goal of a 50-year operating lifetime under the ac bipolar condition determines Analog Devices recommended maximum working voltage. In the case of unipolar ac or dc voltage, the stress on the insulation is significantly lower. This allows operation at higher working voltages while still achieving a 50-year service life. The working voltages listed in Table 19 can be applied while maintaining the 50-year minimum lifetime, provided the voltage conforms to either the unipolar ac or dc voltage cases. Any cross-insulation voltage waveform that does not conform to Figure 22 or Figure 23 should be treated as a bipolar ac waveform, and its peak voltage should be limited to the 50-year lifetime voltage value listed in Table 19.

Note that the voltage presented in Figure 22 is shown as sinusoidal for illustration purposes only. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.



OUTLINE DIMENSIONS



ORDERING GUIDE

	Number	Number	Maximum	Maximum	Maximum	_		
Model ^{1, 2}	of Inputs, V _{DD1} Side	of Inputs, V _{DD2} Side	Data Rate (Mbps)	Propagation Delay, 5 V (ns)	Pulse Width Distortion (ns)	Temperature Range	Package Description	Package Option
ADuM4400ARWZ	4	0	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4400ARWZ-RL	4	0	1	100	40	-40° C to $+105^{\circ}$ C	16-Lead SOIC_W	RW-16
ADuM4400BRWZ	4	0	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4400BRWZ-RL	4	0	10	50	3	-40° C to $+105^{\circ}$ C	16-Lead SOIC W	RW-16
ADuM4400CRWZ	4	0	90	32	2	-40° C to $+105^{\circ}$ C	16-Lead SOIC W	RW-16
ADuM4400CRWZ-RL	4	0	90	32	2	-40° C to $+105^{\circ}$ C	16-Lead SOIC W	RW-16
ADuM4400ARIZ	4	0	1	100	40	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4400ARIZ-RL	4	0	1	100	40	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4400BRIZ	4	0	10	50	3	-40°C to +105°C	16-Lead SOIC IC	RI-16-2
ADuM4400BRIZ-RL	4	0	10	50	3	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4400CRIZ	4	0	90	32	2	-40°C to +105°C	16-Lead SOIC IC	RI-16-2
ADuM4400CRIZ-RL	4	0	90	32	2	-40°C to +105°C	16-Lead SOIC IC	RI-16-2
ADuM4401ARWZ	3	1	1	100	40	-40°C to +105°C	16-Lead SOIC W	RW-16
ADuM4401ARWZ-RL	3	1	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4401BRWZ	3	1	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4401BRWZ-RL	3	1	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4401CRWZ	3	1	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4401CRWZ-RL	3	1	90	32	2	-40°C to +105°C	16-Lead SOIC W	RW-16
ADuM4401ARIZ	3	1	1	100	40	-40°C to +105°C	16-Lead SOIC IC	RI-16-2
ADuM4401ARIZ-RL	3	1	1	100	40	-40°C to +105°C	16-Lead SOIC IC	RI-16-2
ADuM4401BRIZ	3	1	10	50	3	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4401BRIZ-RL	3	1	10	50	3	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4401CRIZ	3	1	90	32	2	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4401CRIZ-RL	3	1	90	32	2	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402ARWZ	2	2	1	100	40	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4402ARWZ-RL	2	2	1	100	40	-40°C to +105°C	16-Lead SOIC W	RW-16
ADuM4402BRWZ	2	2	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4402BRWZ-RL	2	2	10	50	3	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4402CRWZ	2	2	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4402CRWZ-RL	2	2	90	32	2	-40°C to +105°C	16-Lead SOIC_W	RW-16
ADuM4402ARIZ	2	2	1	100	40	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402ARIZ-RL	2	2	1	100	40	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402BRIZ	2	2	10	50	3	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402BRIZ-RL	2	2	10	50	3	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402CRIZ	2	2	90	32	2	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2
ADuM4402CRIZ-RL	2	2	90	32	2	-40°C to +105°C	16-Lead SOIC_IC	RI-16-2

¹ Tape and reel is available. The addition of an -RL suffix designates a 13" (1,000 units) tape and reel option. 2 Z = RoHS Compliant Part.

NOTES



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